

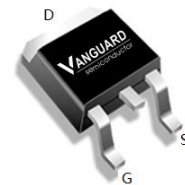
Features

- P-Channel, -5V Logic Level Control
- Low on-resistance RDS(on) @ VGS=-4.5 V
- Fast Switching
- Enhancement mode
- 100% Avalanche Tested
- Pb-free lead plating; RoHS compliant

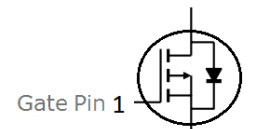


Part ID	Package Type	Marking	Tape and reel information
VSD014P04MS	TO-252	014P04M	2500PCS/Reel

V_{DS}	-40	V
$R_{DS(on),TYP} @ V_{GS}=-10\text{ V}$	13.5	m Ω
$R_{DS(on),TYP} @ V_{GS}=-4.5\text{ V}$	16.5	m Ω
I_D	-55	A

TO-252


Drain Pin 2



Source Pin 3

Maximum ratings, at $T_j = 25^\circ\text{C}$, unless otherwise specified

Symbol	Parameter	Rating	Unit
$V_{(BR)DSS}$	Drain-Source breakdown voltage	-40	V
I_S	Diode continuous forward current	$T_A = 25^\circ\text{C}$ -55	A
I_D	Continuous drain current @ $V_{GS} = -10\text{V}$	$T_A = 25^\circ\text{C}$ -55	A
		$T_A = 100^\circ\text{C}$ -35	A
I_{DM}	Pulse drain current tested ①	$T_A = 25^\circ\text{C}$ -220	A
EAS	Avalanche energy, single pulsed ②	100	mJ
P_D	Maximum power dissipation	$T_A = 25^\circ\text{C}$ 62.5	W
V_{GS}	Gate-Source voltage	± 20	V
$T_{STG} T_J$	Storage and operating temperature range	-55 to 150	$^\circ\text{C}$
Thermal Characteristics			
$R_{\theta JC}$	Thermal Resistance-Junction to Case	2.0	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance Junction-Ambient	100	$^\circ\text{C/W}$

Symbol	Parameter	Condition	Min.	Typ.	Max.	Unit
Static Electrical Characteristics @ T_J = 25°C (unless otherwise stated)						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250μA	-40	--	--	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =-40V, V _{GS} =0V	--	--	-1	μA
	Zero Gate Voltage Drain Current(T _J =125°C)	V _{DS} =-40V, V _{GS} =0V	--	--	-100	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±20V, V _{DS} =0V	--	--	±100	nA
V _{GS(TH)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =-250μA	-1.0	-1.6	-2.5	V
R _{DS(ON)}	Drain-Source On-State Resistance ③	V _{GS} =-10V, I _D =-15A	--	13.5	17	mΩ
R _{DS(ON)}	Drain-Source On-State Resistance ③	V _{GS} =-4.5V, I _D =-10A	--	16.5	20	mΩ
Dynamic Electrical Characteristics @ T_J = 25°C (unless otherwise stated)						
C _{iss}	Input Capacitance	V _{DS} =-20V, V _{GS} =0V, f=1MHz	--	3000	--	pF
C _{oss}	Output Capacitance		--	320	--	pF
C _{rss}	Reverse Transfer Capacitance		--	210	--	pF
R _g	Gate Resistance	f=1MHz		15.6		Ω
Q _g	Total Gate Charge	V _{DS} =-20V, I _D =-15A, V _{GS} =-10V	--	59	--	nC
Q _{gs}	Gate-Source Charge		--	11	--	nC
Q _{gd}	Gate-Drain Charge		--	12	--	nC
Switching Characteristics						
t _{d(on)}	Turn-on Delay Time	V _{DD} =-20V, I _D =-15A, R _G =3.0Ω, V _{GS} =-10V	--	8.6	--	nS
t _r	Turn-on Rise Time		--	11	--	nS
t _{d(off)}	Turn-Off Delay Time		--	51	--	nS
t _f	Turn-Off Fall Time		--	14	--	nS
Source- Drain Diode Characteristics @ T_J = 25°C (unless otherwise stated)						
V _{SD}	Forward on voltage	I _{SD} =-15A, V _{GS} =0V	--	-0.85	-1.2	V
t _{rr}	Reverse Recovery Time	T _J =25°C, I _{sd} =-15A, V _{GS} =0V	--	13	--	nS
Q _{rr}	Reverse Recovery Charge	di/dt=-500A/μs		21		nC

NOTE:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Limited by T_{Jmax}, starting T_J = 25°C, L = 0.5mH, R_G = 25Ω, I_{AS} = -20A, V_{GS} = -10V. Part not recommended for use above this value
- ③ Pulse width ≤ 300μs; duty cycle ≤ 2%.

Typical Characteristics

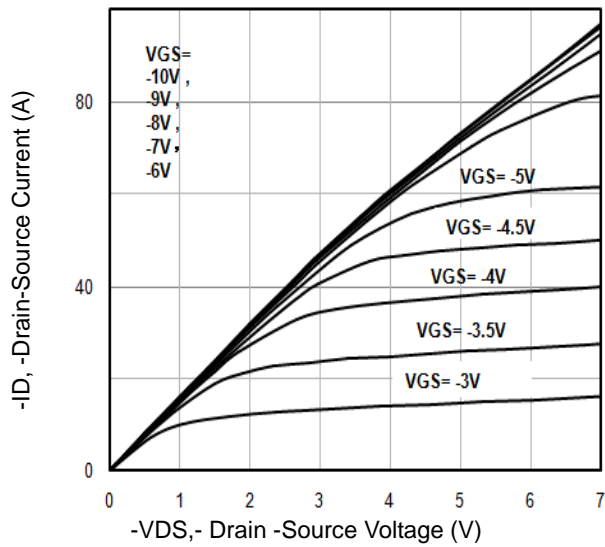


Fig1. Typical Output Characteristics

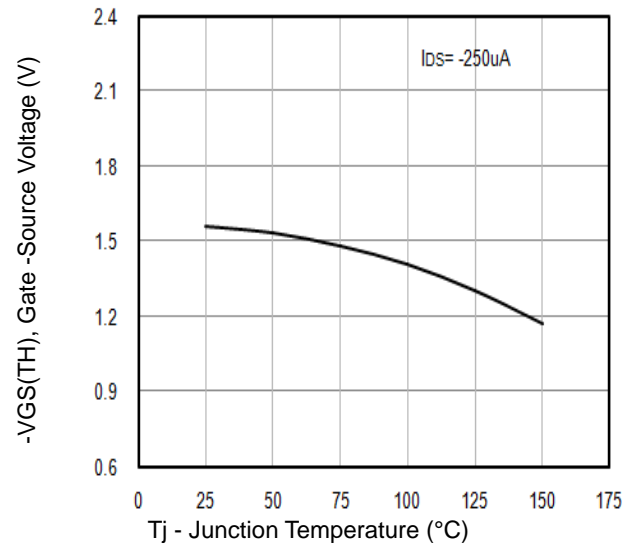


Fig2. $-V_{GS(TH)}$ Gate -Source Voltage Vs. T_j

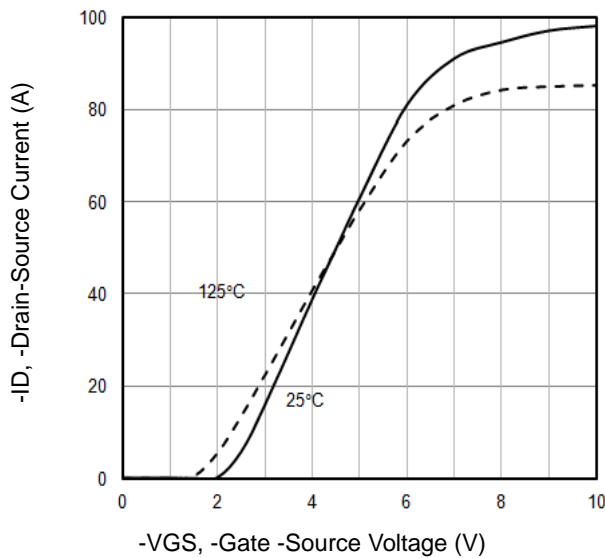


Fig3. Typical Transfer Characteristics

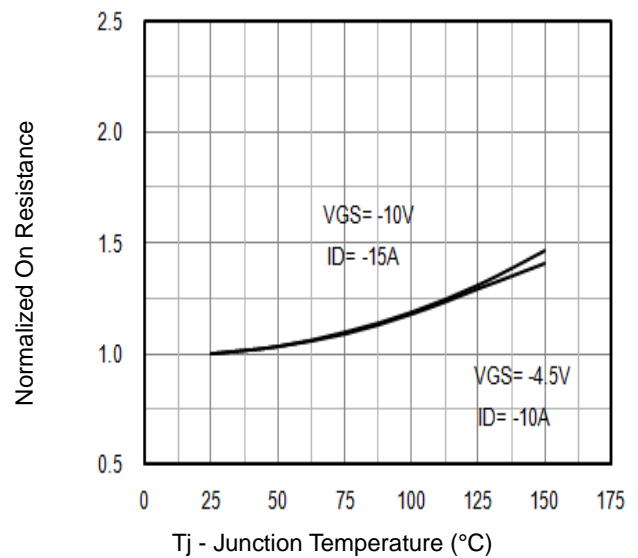


Fig4. Normalized On-Resistance Vs. T_j

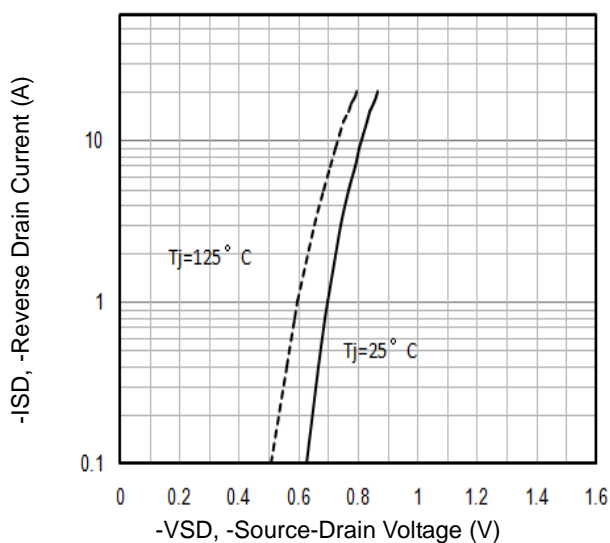


Fig5. Typical Source-Drain Diode Forward Voltage

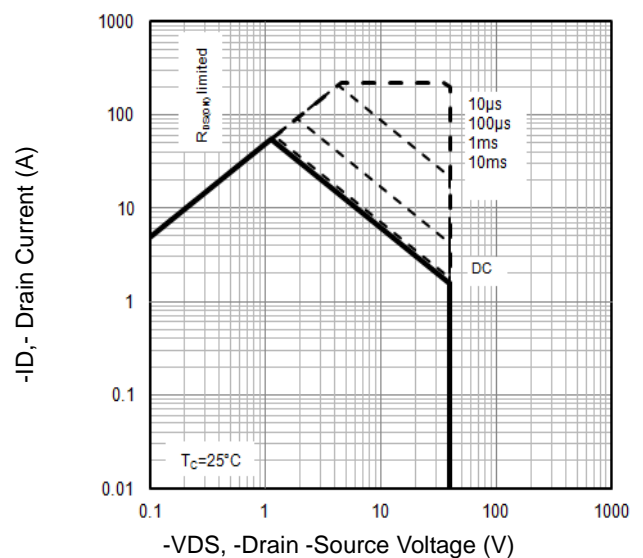


Fig6. Maximum Safe Operating Area

Typical Characteristics

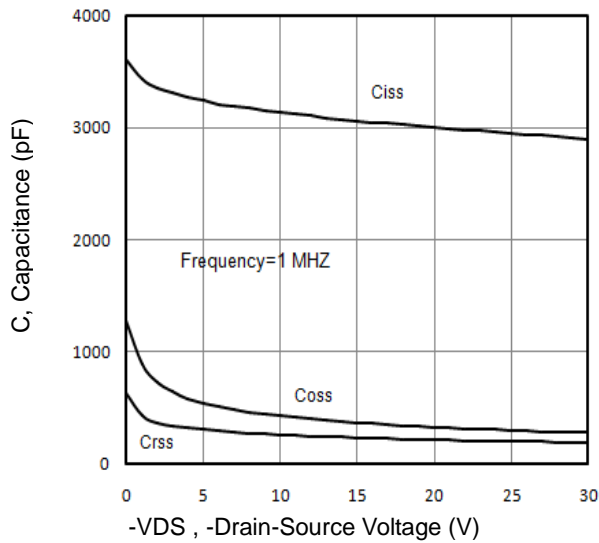


Fig7. Typical Capacitance Vs.Drain-Source Voltage

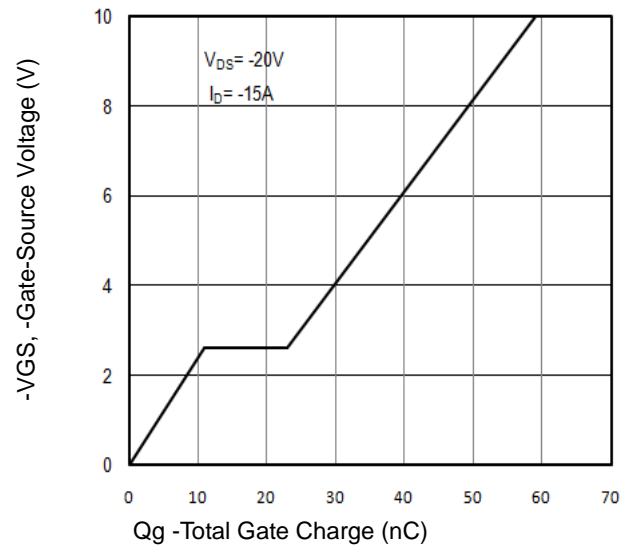


Fig8. Typical Gate Charge Vs.Gate-Source Voltage

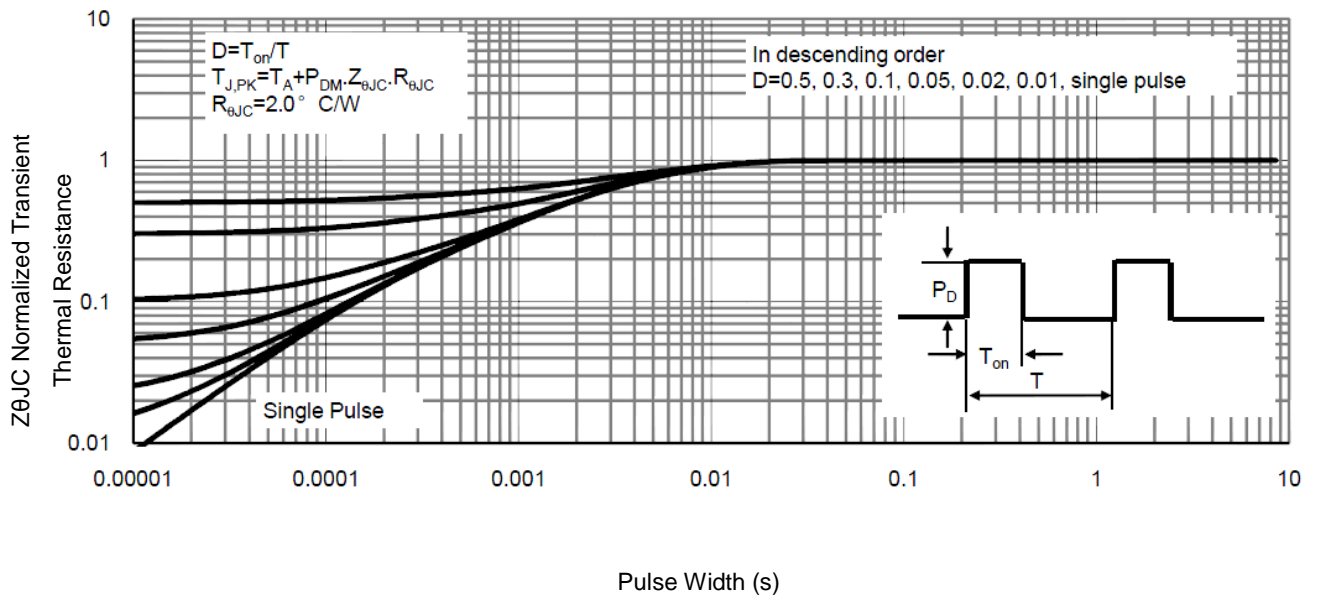


Fig9. Normalized Maximum Transient Thermal Impedance

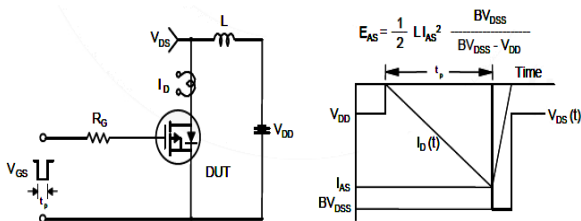


Fig10. Unclamped Inductive Test Circuit and Waveforms

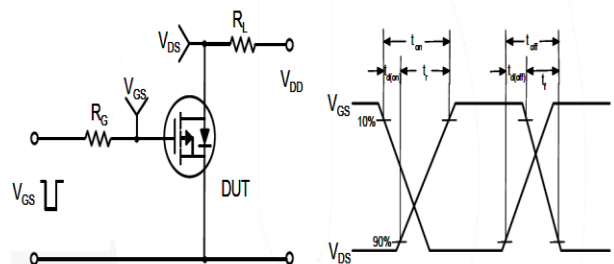
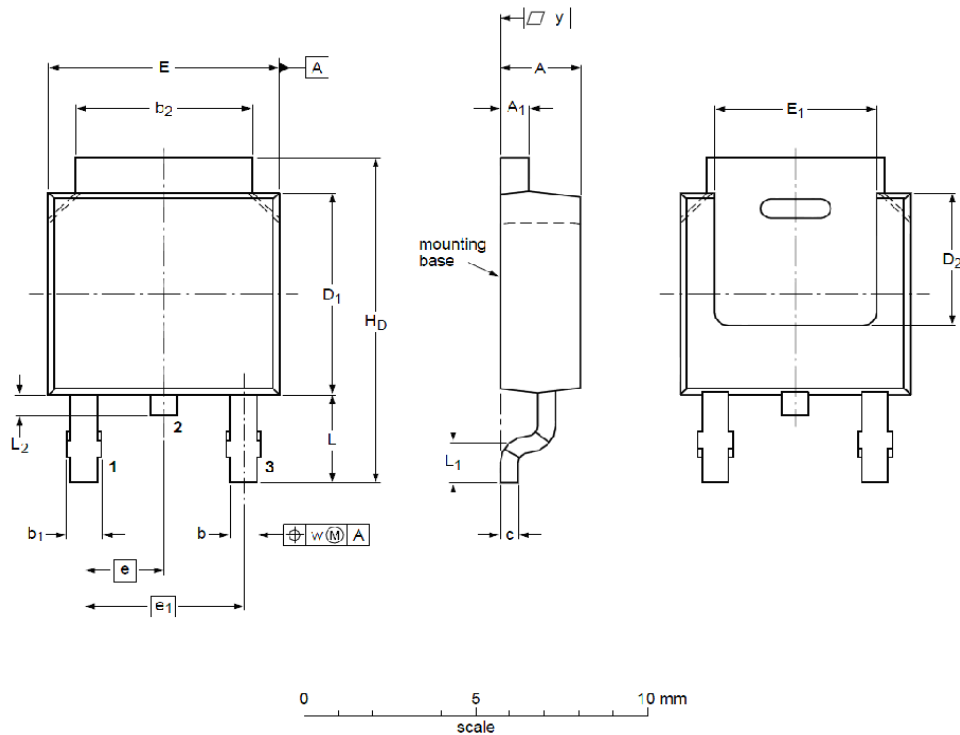


Fig11. Switching Time Test Circuit and waveforms

TO-252 Package Outline Data



DIMENSIONS (unit : mm)

Symbol	Min	Typ	Max	Symbol	Min	Typ	Max
A	2.22	2.30	2.38	A ₁	0.46	0.58	0.93
b	0.71	0.79	0.89	b ₁	0.90	0.98	1.10
b ₂	5.00	5.30	5.46	c	0.20	0.40	0.56
D ₁	5.98	6.05	6.22	D ₂	--	4.00	--
E	6.47	6.60	6.73	E ₁	5.10	5.28	5.45
e	--	2.28	--	e ₁	--	4.57	--
H _b	9.60	10.08	10.40	L	2.75	2.95	3.05
L ₁	--	0.50	--	L ₂	0.80	0.90	1.10
w	--	0.20	--	y	0.20	--	--

Customer Service

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